the United States Patent and Trademark Office JIM 3 1 7671

Aratani et al. Applicants:

Examiner R. McDonald

Serial No.: 09/429,719

Group Unit: 1753

Title:

Thin Film Formation Use Sputtering ...

Atty. Docket No. 9792486-0010 (formerly P99,2247)

17X1-5/36/61

In response to the First Office Action dated, 24 July 2000, the applicants respond as Told 25 2007

follows.

A. In the Claims:

1. (Amended) A method of forming a thin film comprising the step of: forming an AgP thin film using a sputtering target material, [wherein] the AgPd alloy thin film comprises Pd in an amount ranging from 0.5 to 4.9 atomic %; and irradiating an information recording layer with a light beam having a wavelength of less than or equal to 800 nm.

- 7. (Amended) A method of forming a thin film comprising the step of: forming an AgPdTi alloy thin film using a sputtering target material, [wherein] the AgPdTi alloy comprises Pd in an amount ranging from 0.1 to 1.5 atomic % and Ti in an amount ranging from 0.1 to 2.9 atomic %; and irradiating an information recording layer with a light beam having a wavelength of less than or equal to 800 nm.
- 8. (New) The method of claim 1, wherein the wavelength is less than or equal to 650 nm.
- 9. (New) The method of claim 2, wherein the wavelength is less than or equal to 650 nm.